



Oven Controlled Crystal Oscillator (OCXO)

■ NH37M28LN Data Sheet

Main Application

- Base stations for system mobile communications (5G CU, 4G BBU)
- IEEE1588, Synchronous Ethernet clock (SyncE)
- Optical transmission systems Stratum 3E
- Frequency synthesizer
- GNSS-DO
- Timing and synchronous measuring equipment
- High resolution audio clock

Features

- Low height and excellent temperature characteristics.
- Supports wide temperature range.
- Excellent holdover characteristics.
- Frequency adjustment by digital control method (I²C Control).
(Voltage control method (V_{cont}) is also possible.)
- Dimension : 37 × 28 × 12.7 mm



RoHS Compliant
Directive 2011/65/EU
Directive (EU) 2015/863

1. Item : Oven Controlled Crystal Oscillator (OCXO)
2. Type : NH37M28LN
3. Nominal Frequency: 10 MHz
4. NDK Spec. No. : NSA3650A, NSA3649A
Please refer to sections 5 and 6 as the ratings and electrical specifications change depending on NDK spec. No.
5. Rating

| Parameters | Sym. | Spec. | | | | Notes |
|---------------------------------|------------|----------|----------|------------|-------|---|
| | | Min. | Typ. | Max. | Units | |
| 5.1 Nominal Frequency | f_{nom} | 10 | | | MHz | |
| 5.2 Supply Voltage | V_{CC} | +4.75 | +5.0 | +5.25 | V | |
| 5.3 Control Voltage | V_{cont} | 0 | +2.5 | +5.0 | V | NSA3650A |
| | | 0x800000 | 0x000000 | 0x7FFFFFFF | - | NSA3649A 2's complement. In detail, refer to the section 7 |
| 5.4 Load | C_L | - | 15 | - | pF | |
| 5.5 Operating Temperature Range | T_{opr} | -40 | - | +85 | °C | |
| 5.6 Storage Temperature Range | T_{str} | -40 | - | +85 | °C | |

6. Electrical Specifications

Unless otherwise specified, meaning condition. $T = +25\text{ °C}$, $V_{CC} = +5.0\text{ V}$, $V_{cont} = \text{Center}$, $C_L = 15\text{ pF}$

| Parameters | Sym. | Spec. | | | | Conditions |
|---|--------------------|-------|------|------|-------|---|
| | | Min. | Typ. | Max. | Units | |
| 6.1 Power Consumption | | | | | | |
| 6.1.1 During Warm-up | P_{CC} | - | 3.0 | 3.5 | W | |
| 6.1.2 Steady State | P_{CC} | - | - | 1.6 | W | $T = +25\text{ °C}$ |
| 6.2 Frequency Stability | | | | | | |
| 6.2.1 Frequency Tolerance | $\Delta f/f_{nom}$ | -25 | - | +25 | ppb | (*1) |
| 6.2.2 Frequency/Temperature Characteristics | $\Delta f/f$ | -0.5 | - | +0.5 | ppb | at Operating Temperature Range (*2) NSC5211A, NSC5212A |
| 6.2.3 Frequency/Voltage Coefficient | $\Delta f/f$ | -0.2 | - | +0.2 | ppb | $V_{CC} = +5.0\text{ V} \pm 5\%$ (*2) |
| 6.2.4 Long-term Frequency stability | $\Delta f/f$ | -0.2 | - | +0.2 | ppb | 1 day (*3) |
| | | -50 | - | +50 | ppb | 1 year (*3) |
| 6.2.5 Stabilization Time | - | - | - | 5 | min. | (*4) |
| 6.2.6 Holdover | - | - | 1.0 | - | us | 8 h (*5) |

| Parameters | Sym. | Spec. | | | | Conditions |
|---------------------------|------------------------|----------------------|------|------|--------|-------------------------------|
| | | Min. | Typ. | Max. | Units | |
| 6.3 | Frequency Control | | | | | |
| 6.3.1 | - | Positive Slope | | | | - |
| 6.3.2 | $\Delta f/f$ | -0.5 | - | -0.3 | ppm | $V_{cont} = \text{Min. (*2)}$ |
| 6.3.2 | | +0.3 | - | +0.5 | ppm | $V_{cont} = \text{Max. (*2)}$ |
| 6.3.3 | - | - | - | 5 | % | |
| 6.4 | Output Characteristics | | | | | |
| 6.4.1 | - | LVCMOS (Square wave) | | | | |
| 6.4.2 | | | | | | |
| High Level Output Voltage | V_{OH} | +2.4 | - | - | V | |
| Low Level Output Voltage | V_{OL} | - | - | +0.4 | V | |
| 6.4.3 | - | 45 | - | 55 | % | at $(V_{OH} + V_{OL})/2$ |
| 6.5 | | | | | | |
| Phase Noise | L(f) | - | -83 | - | dBc/Hz | 1 Hz offset |
| at 10 MHz | | - | -110 | - | dBc/Hz | 10 Hz offset |
| | | - | -135 | - | dBc/Hz | 100 Hz offset |
| | | - | -152 | - | dBc/Hz | 1 kHz offset |
| | | - | -157 | - | dBc/Hz | 10 kHz offset |
| | | - | -160 | - | dBc/Hz | 100 kHz offset |

(*1) $\Delta f/f_{nom}$: : Frequency shift from nominal frequency.

(*2) $\Delta f/f$: Frequency shift from the reference frequency.

T = +25 °C, $V_{CC} = +5.0$ V, $V_{cont} = \text{Center}$, $C_L = 15$ pF

(*3) Based on frequency after 7 days operation.

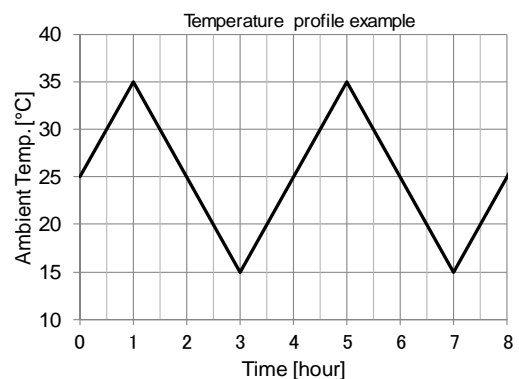
(*4) Within ± 10 ppb, based on frequency after 60 minutes. T = +25 °C.

(*5) Conditions for Holdover

Based on frequency after 7 days operation

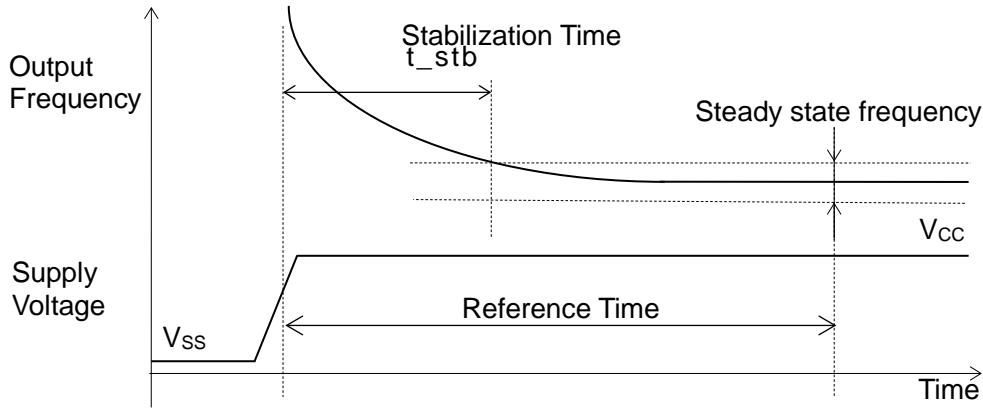
Temperature range: 20 °C window

Temperature slope: 10 °C/hour

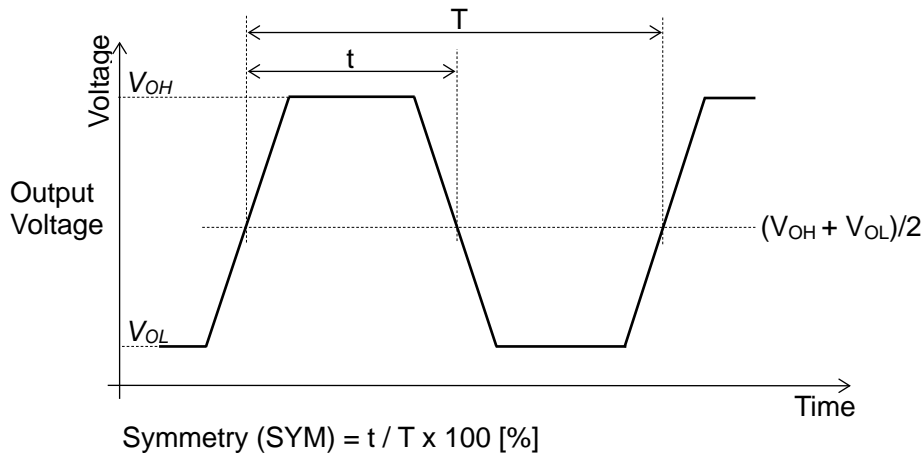


(*6) Typ. Value is for reference only.

Stabilization Time



Waveform



7. Digital Frequency Tuning (NSA3649A)

7.1 Relation Registers

| No. | Register address (hex) | Contents | Initial value after reset (hex) |
|-----|------------------------|-------------------------------------|---------------------------------|
| 1 | C0 | V_{cont} register (bit 23 to 16) | 00 |
| 2 | C1 | V_{cont} register (bit 15 to 8) | 00 |
| 3 | C2 | V_{cont} register (bit 7 to 0) | 00 |
| 4 | C3 | Triger (refer to the section 7.2.4) | 00 |

7.2 How to Set the Registers

| No. | Item | Contents |
|-----|---|--|
| 1 | To calculate frequency tuning range per 1 bit | Calculating formula: To set $A = (\text{Frequency tuning range}) / 2^{24}$ e.g.: 400 ppb (i.e. ± 200 ppb) / $2^{24} = 0.024$ ppt / bit |
| 2 | To calculate register value from frequency tuning value | Calculation formula: To set $B = \text{round} \{(\text{Frequency tuning value}) / A\}$ e.g.: If your requested frequency tuning value is 25 ppb, $\text{round} \{(25 \text{ ppb}) / 0.024 \text{ ppt}\} = B = 1,041,666$ |
| 3 | To convert the calculated register value to 3 bytes hex by 2's complement | e.g.1: +512 = 00 02 00 (hex) e.g.2: -4096 = FF F0 00 (hex) Note: Please set a limiter by 0x7FFFFFFF and 0x800000 to avert an overflow. |
| 4 | To write 4 bytes: addresses C0, C1, C2 and C3 | Note: Data in addresses C0 to C2 are written only after data is written in address C3 00(hex). |

7.3 Note for digital frequency tuning

A frequency tuning value which written in the addresses in the section 7.1 by the setting method in the section 7.2 are not saved to a non-volatile memory.

Therefore, please calculate in the section 7.2 and set the intended frequency tuning value to an oscillator once every power-on.

7.4 Access method

This oscillator supports the following four access methods:

| No. | Name | Explanation |
|-----|------------------|--|
| 1 | Byte write | To write one byte data to an arbitrary one address in an oscillator. |
| 2 | Sequential write | To write four bytes data to sequential four addresses in an oscillator. |
| 3 | Random read | To read one byte data from an arbitrary one address in an oscillator. |
| 4 | Sequential read | To read four bytes data from arbitrary sequential four addresses in an oscillator. |

Timing charts of each access method is shown as follows:

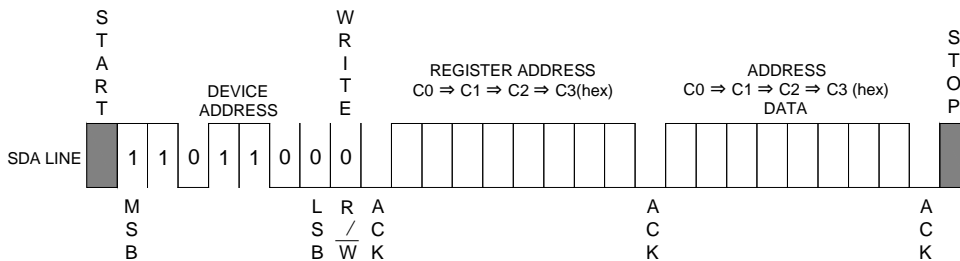


fig. 7.4.1 Byte write

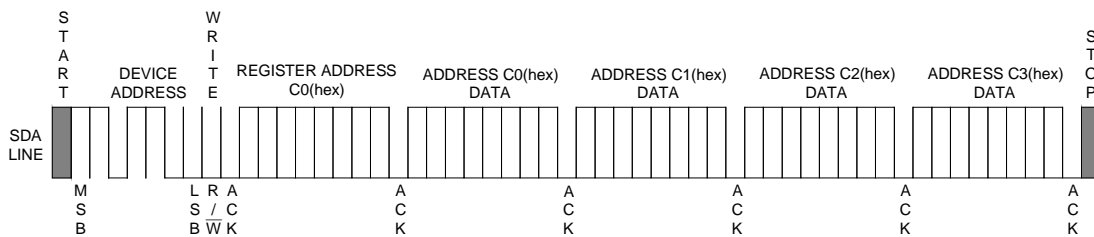


fig7.4.2 Sequential write

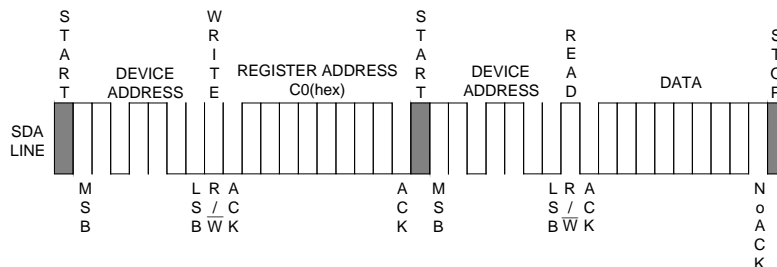


fig7.4.3 Random read